

Exploration COMSOL in Modeling RLSA™ CVD Processes

Ar+H₂+SiH₄+C₂H₆ and Dopant Gas

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outline

- **Radial line slot antenna (RLSA)**
- **Microwave plasma in semiconductor processing tool**
- **Coupling and operation modes**
- **Major challenges – plasma tools**
- **Model – implemented in Plasma Module by COMSOL – user experience**
- **Conclusion remarks**

Conclusion remarks

- The creation of SW discharges is clear example of a self-consistent nonlinear problem and it represents strongly coupled stiffy system
- Solving large number of equations with complex chemistry and coupled wave-plasma physics at the scale of real reactor represents challenge
- **COMPLEXITY OF REACTIVE PLASMA STILL PRESENT!**
- Plasma Module has great capabilities for fast development, modifications, easy GUI, adaptation for new input data and postprocessing

Radial line slot antenna plasma source

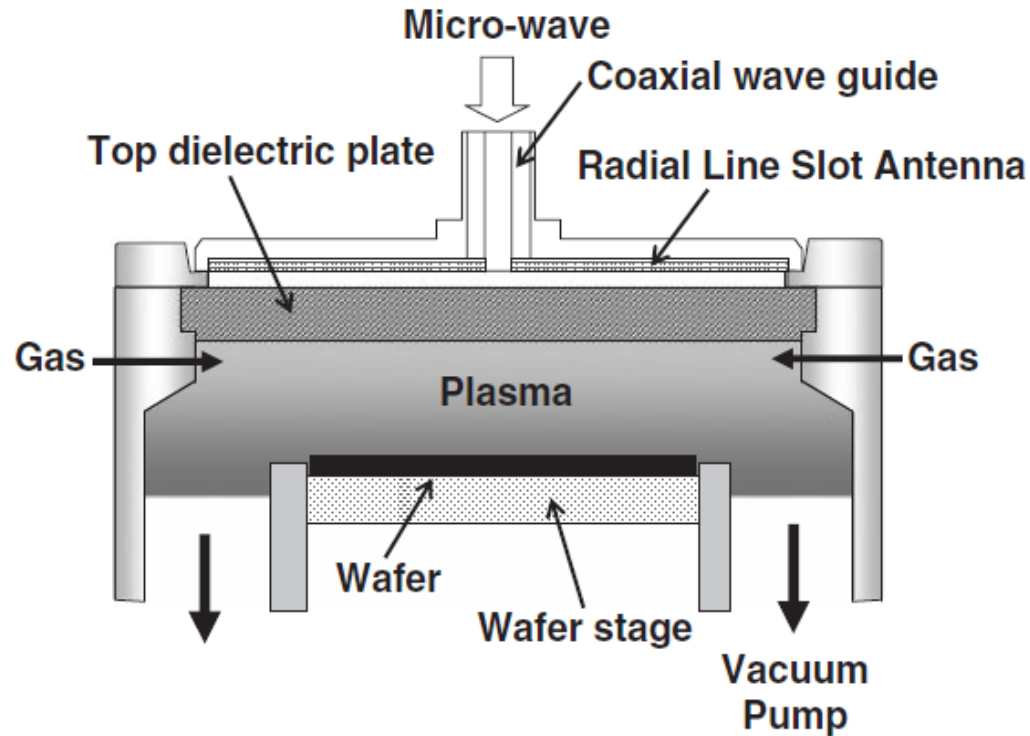
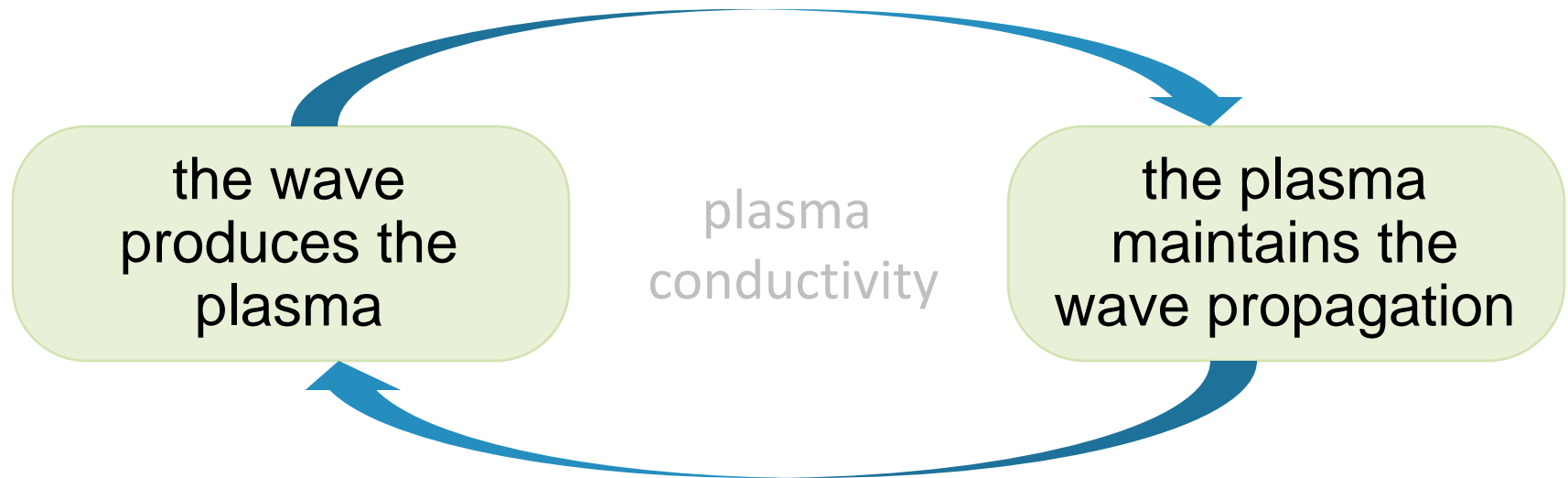


Fig. 1. A cross-sectional view of RLSA PECVD reactor.

Plasma is sustained by 2.45 GHz EM wave distributed by antenna and propagating through processing gas

Physics background

- SW-sustained discharges are structures which unify wave-fields and gas-discharge plasmas



- The discharge behavior is simultaneously governed by electrodynamics and gas discharge physics

Operation modes

Surface
wave mode

Transitional
mode

Resonant
mode

motivation

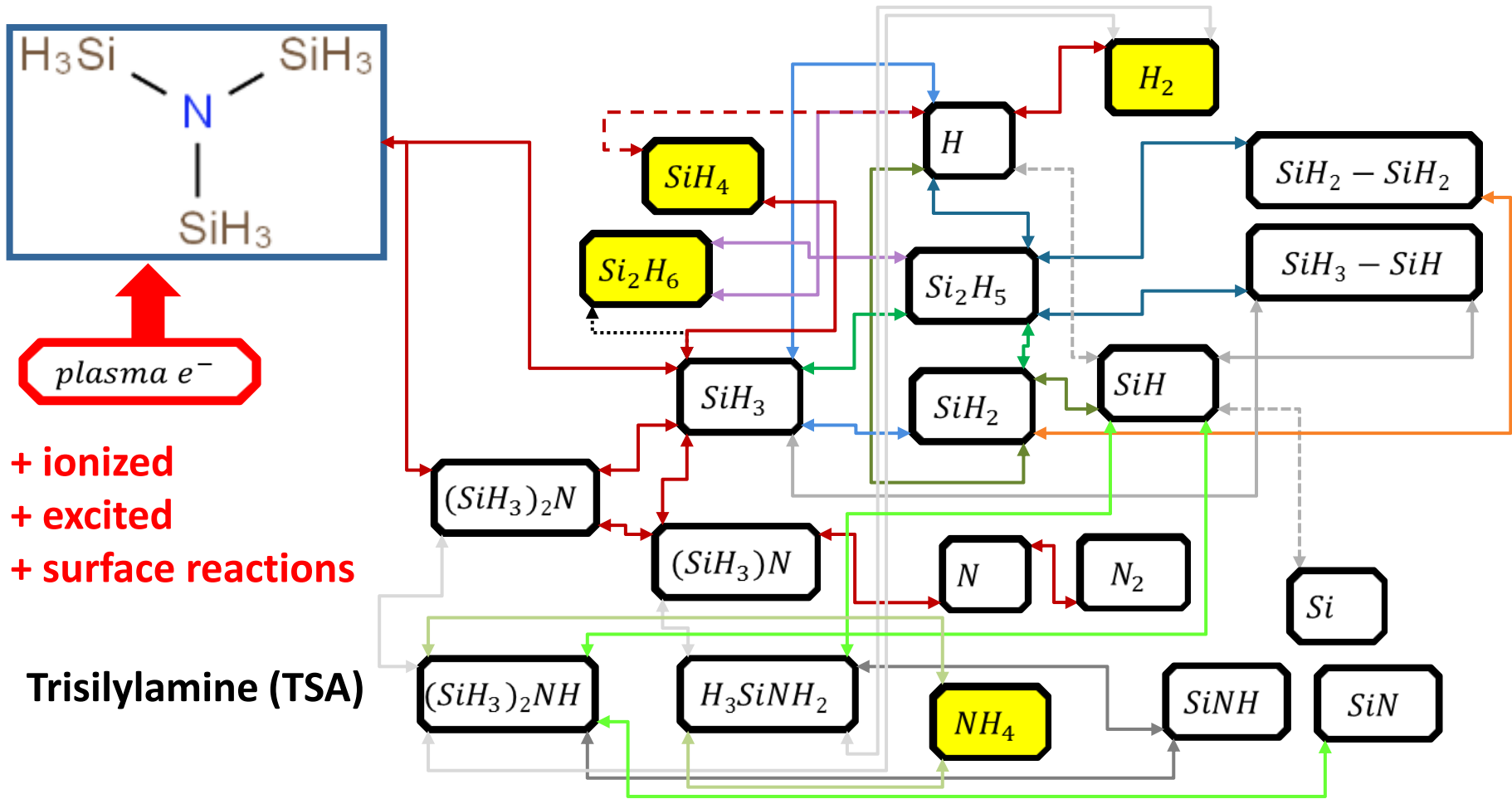
- **New materials, gas mixtures, scale leading to technological process expansion**
- **Non obvious and predictable process outcome**

Challenge

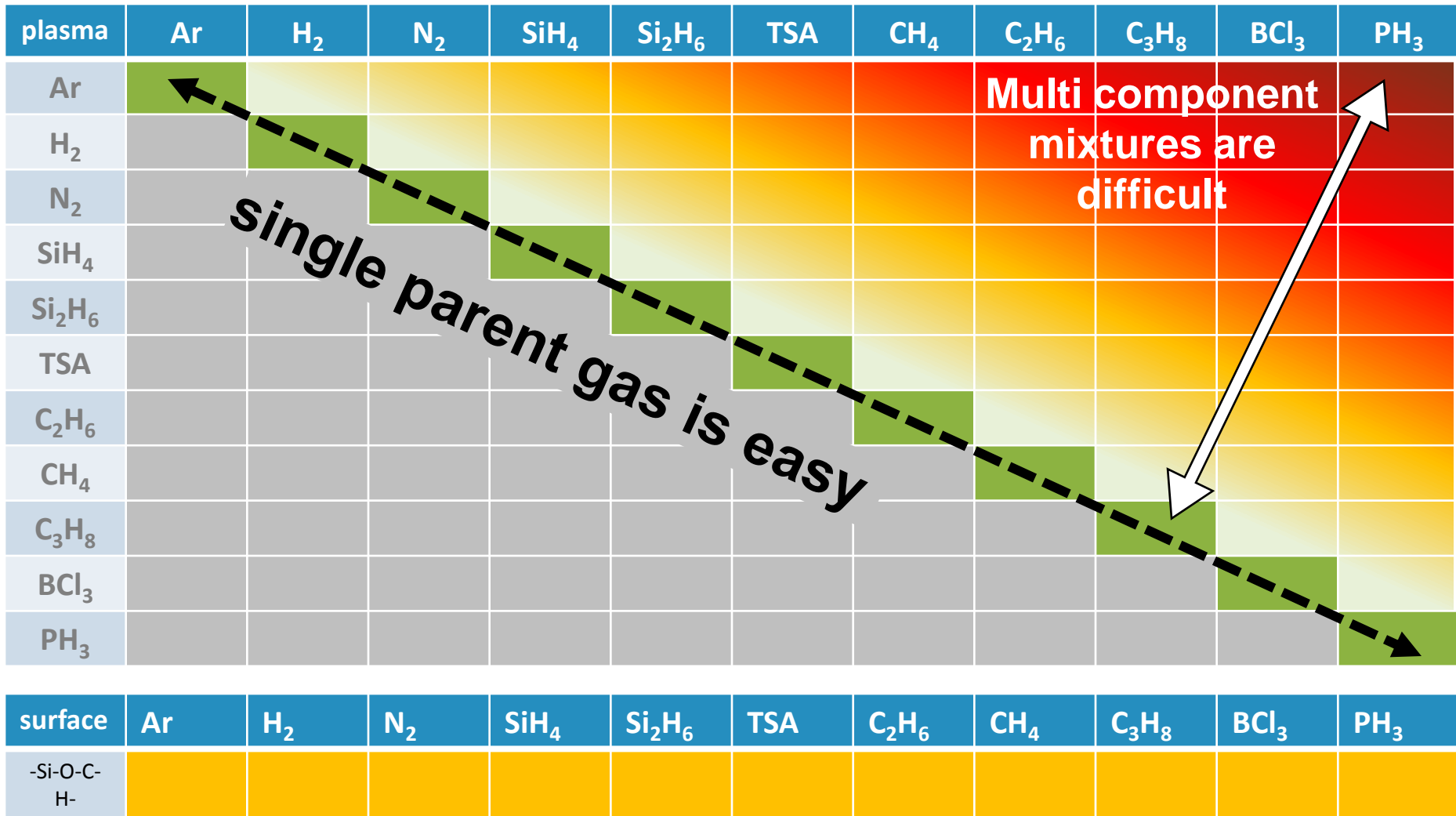
**Complex process
chemistry**

**Scaling plasma
sources**

Reaction models → prediction on process



multispecies and reactions



Chemistry included in current model

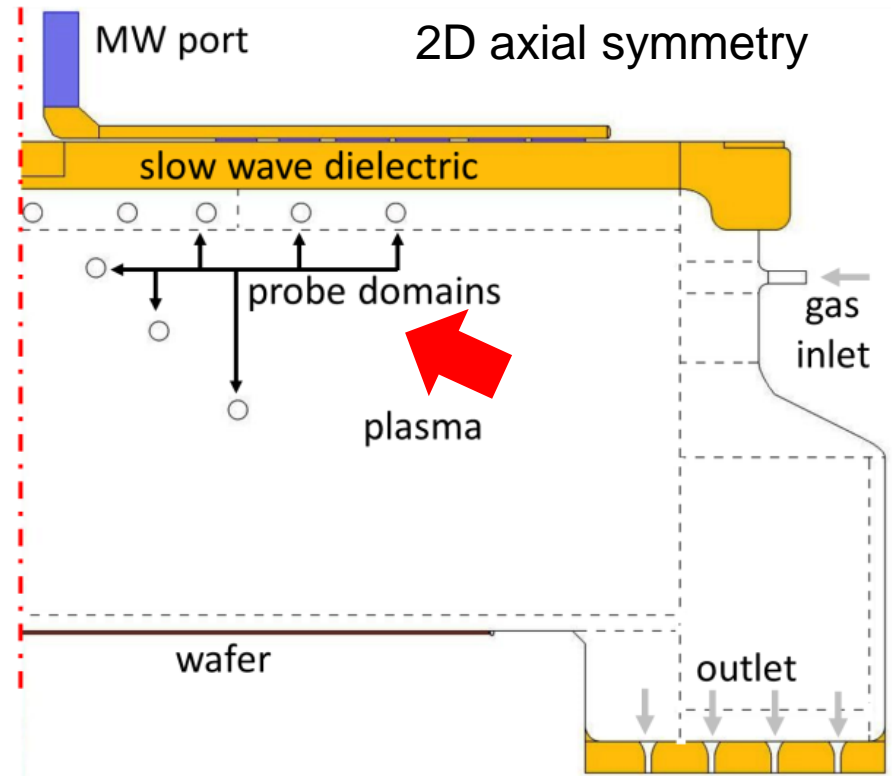
	Ar	H ₂	C ₂ H ₆	Si precursor	Dopants PH ₃ BCl ₃	TOTAL
Number of species	5	25	16	~ 10		~ 56
Plasma reactions	4 ^e (39)	21 ^e +	~25	19	5	~ 73
Homogeneous reactions						~ 5
Surface reactions	2	21 +				~ 23

(e) - primary collisions with electron

- Model becomes substantially larger
- Still some simplifications – grouping similar reactions, excitation levels
- Upgrading chemistry not final - TBD

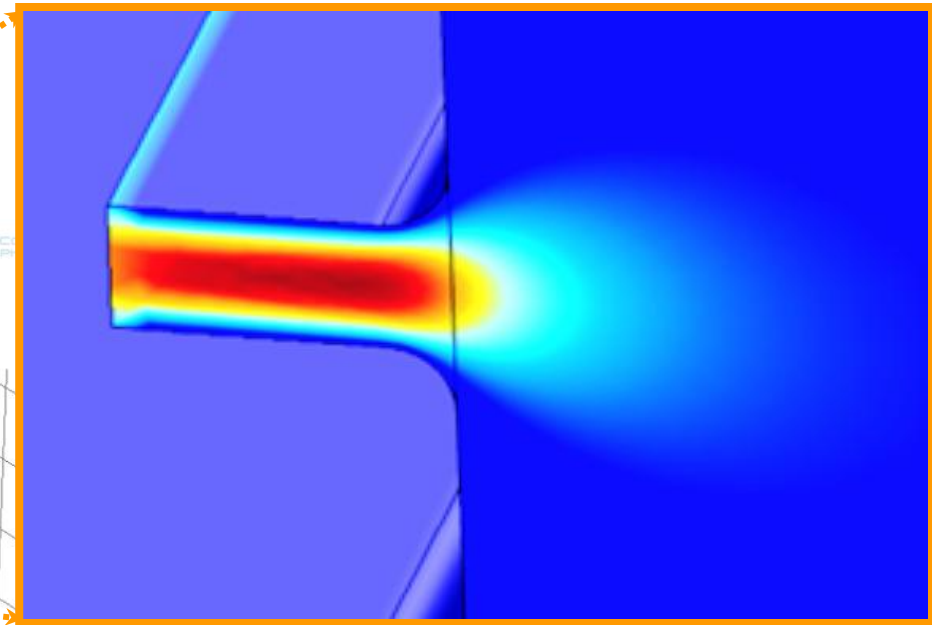
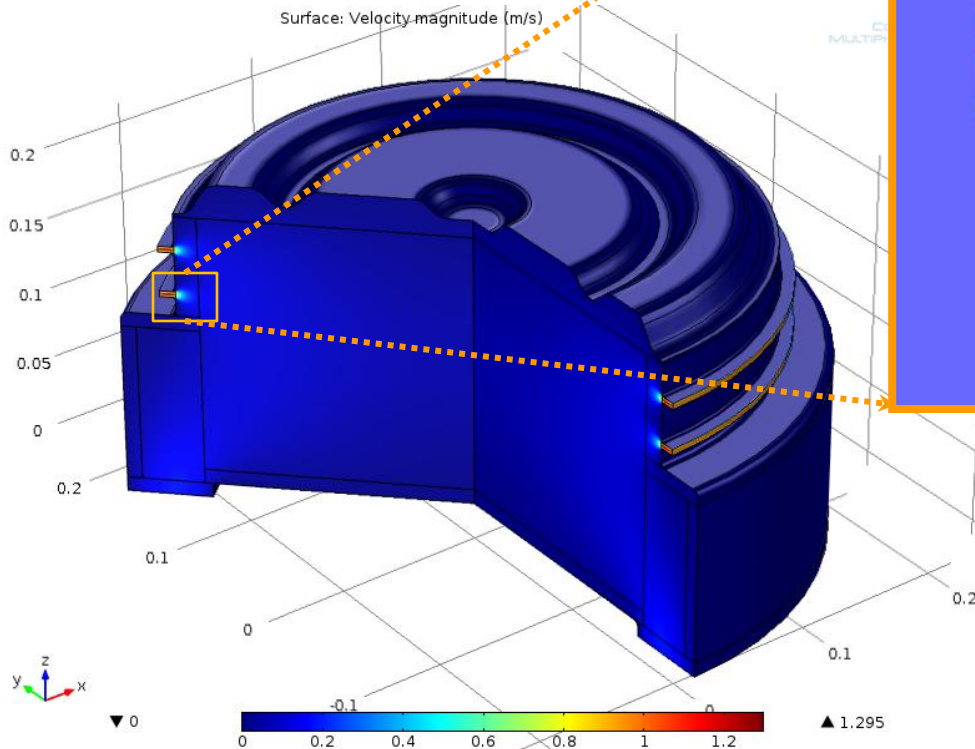
Model geometry and computational environment

- Plasma Module in COMSOL Multiphysics suite ver.4.3.b
- Memory in individual cases is in range from 10 to 50 GB
- Computational time from 4 hours to over 100 hours per case
- Individual transient cases converged typically in range $10^{-3} - 10^{-2}$ s



Gas flow

Compressible flow ($M < 3$) module



- Flow (velocity, pressure)
- Output on plasma parameters (density, temperature, deposited power, composition, ...)
- Thermal capabilities will be built at later stage

Mostly used cross-sections as input

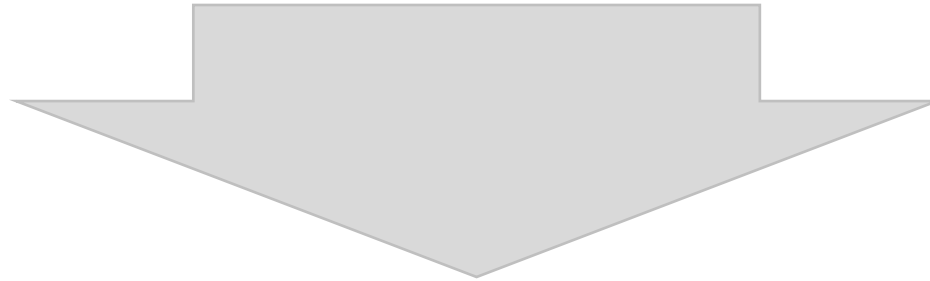
(flexibility to explore EEDF)

- www.lxcat.laplace.univ-tlse.fr
 - *J. Phys. D: Appl. Phys.* 46 334001 (2013)
 - *J. Phys. D: Appl. Phys.* 46 334002 (2013)
 - *J. Phys. D: Appl. Phys.* 46 334003 (2013)
- Data were not always ready to be automatically transformed
- Certain letters used in database may triggered change in data formatting in Comsol, for example, symbol (') triggers “d” and crashing or missinterpretation data ...
- More specific reactions from scientific publications (mostly as reaction rate constants)
- Choosing approach with uploading rather individual cross section data instead of block of cross sections

SW upgrades – check frequently!

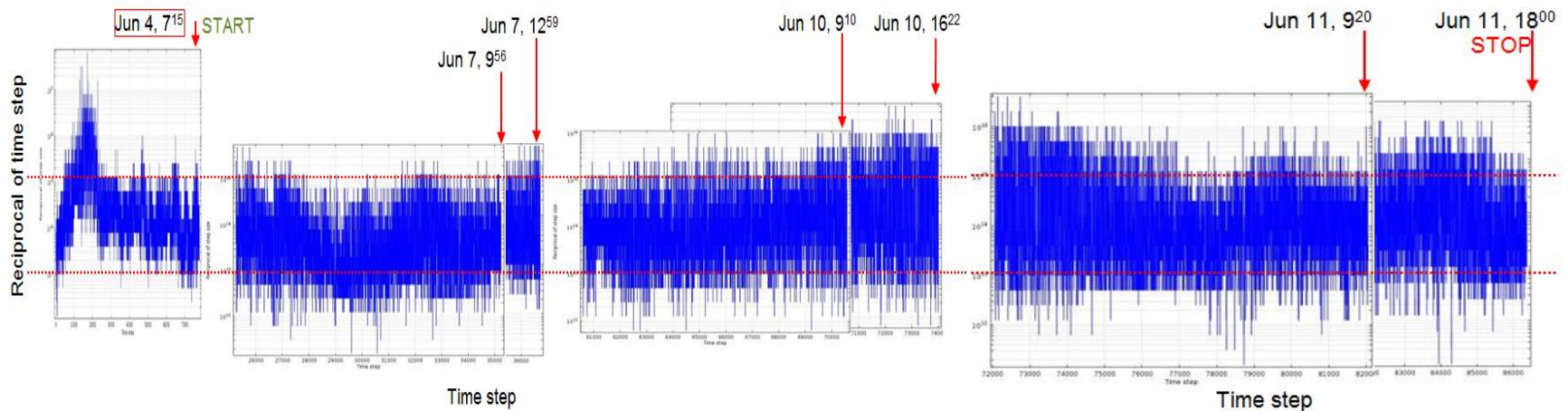
- This work used v.4.3.2.152 and it was upgraded only on Aug 29, 2013 into update v.1.3.2.189
- Upgrade released in end of July 2013

“MWP now works correctly when used with electromagnetic solver !”

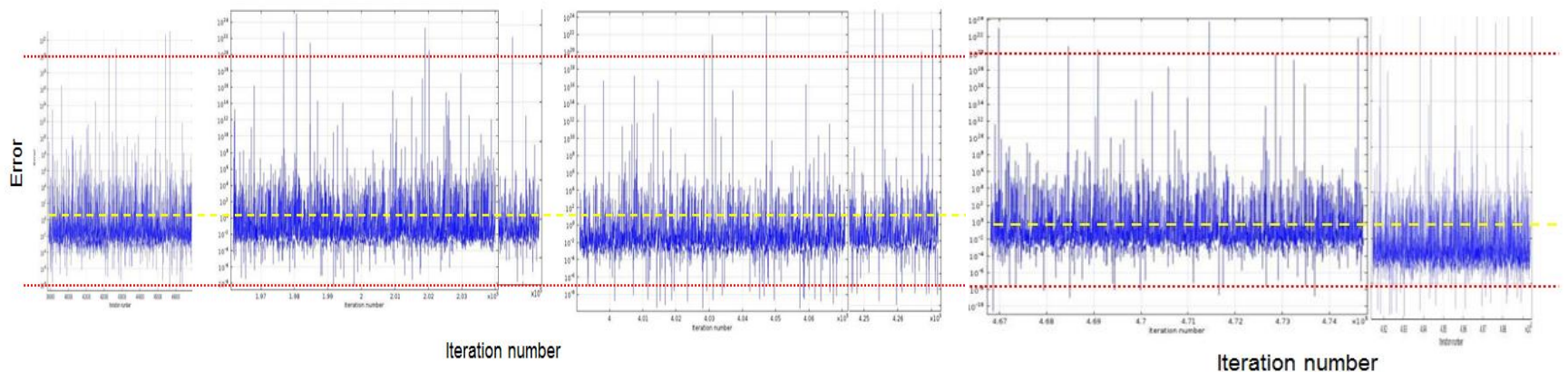


REWORK THAT COULD BE AVOIDED
NEW COMPUTATIONS → DELAY

Convergence timeline – long computations

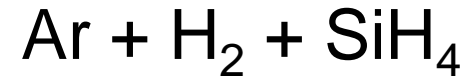
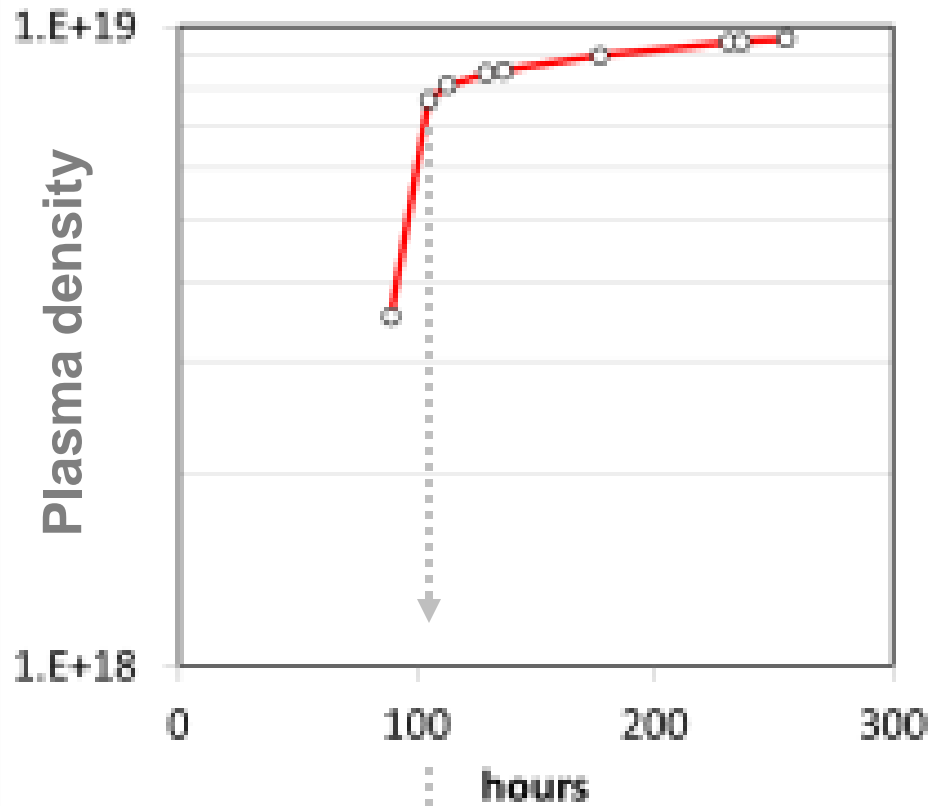


noticeable reduced error but transient computation within picoseconds steps



- meshing and transient settings need to be optimized substantially
- accurate but efficient numerical method is desirable in terms of computation time, especially for an optimization process

Computation time / monitoring probes



Dell Precision WorkStation
T7500 (64bit Windows 7
Enterprise OS, two processors
X5690 – 24 cores, RAM 96
GB)

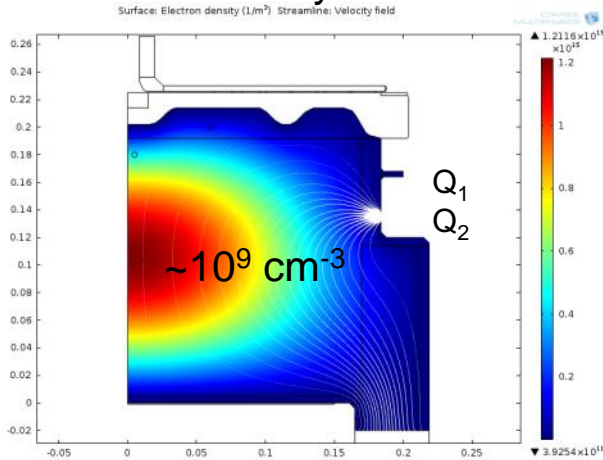
Convergence – highly sensitive
to initial values

It is important wisely predict
initial values to get efficient
convergence

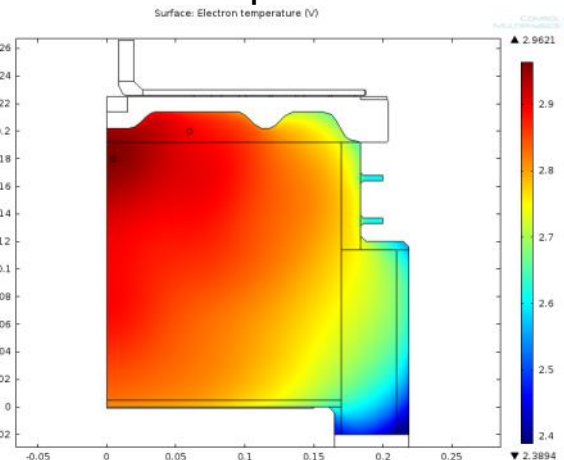
Up to several days
Pressure is critical parameter

Low pressure cases – fast turnaround (several hours)

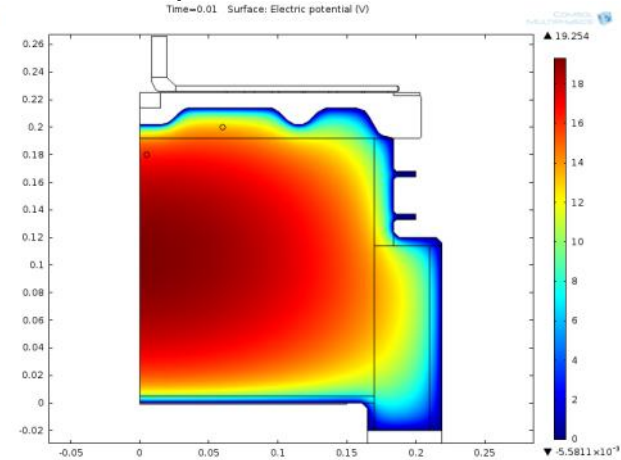
Electron density



Electron temperature



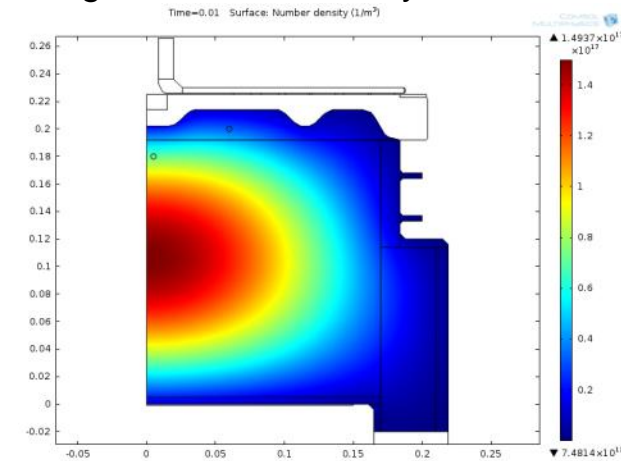
Plasma potential



Ar - 15 mTorr - 1 kW - Q₂/100 sccm

- Low pressure cases – fast turn around (several hours)
- Enhanced chemistry may produce even longer computational times
- Transitional or resonant mode

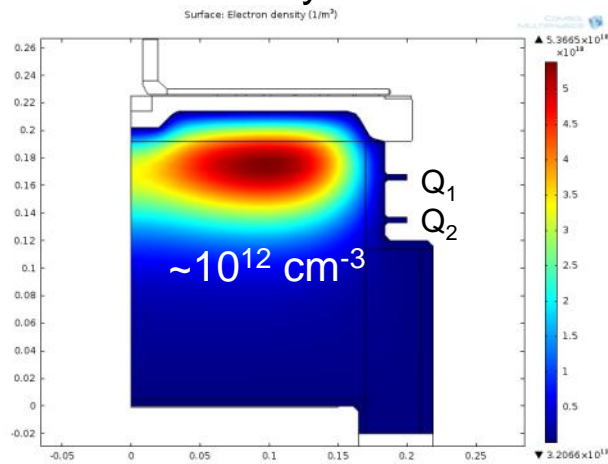
Argon excited / density



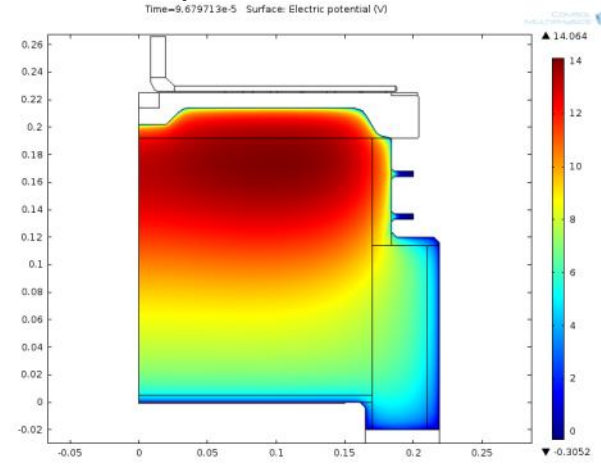
Increased pressure longer convergence (>24+ hours)

Ar - 100 mTorr - 5 kW - Q₁/50 sccm - Q₂/50 sccm

Electron density



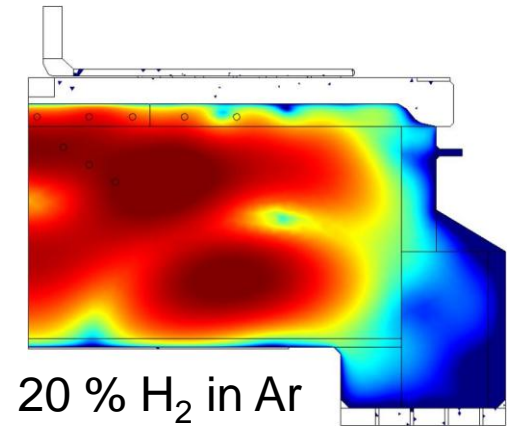
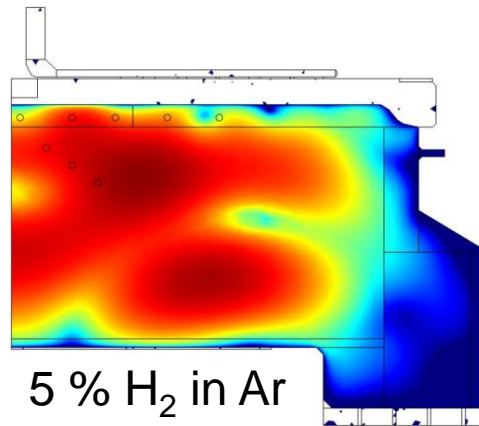
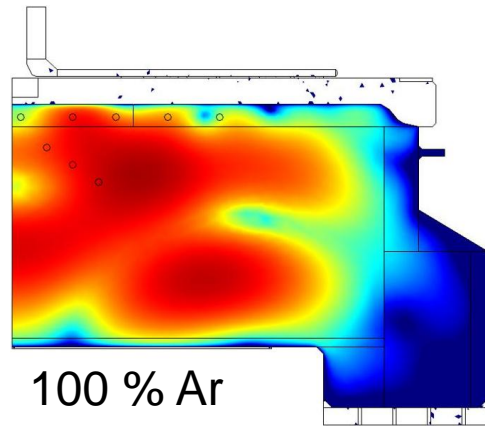
Plasma potential



shown results are not final (10⁻⁴ s)

- Plasma in SW mode

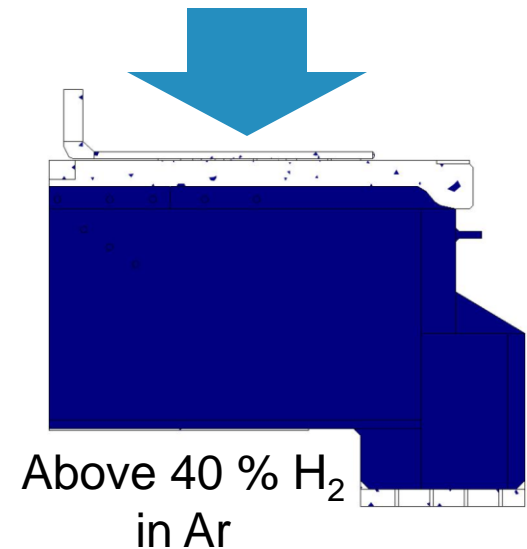
Ar:H₂ resistive loss in plasma



Ar+H₂ only, 50 mTorr, 3.5 kW

Adding H₂ increases the resistive loss in plasma → then convergence is lost

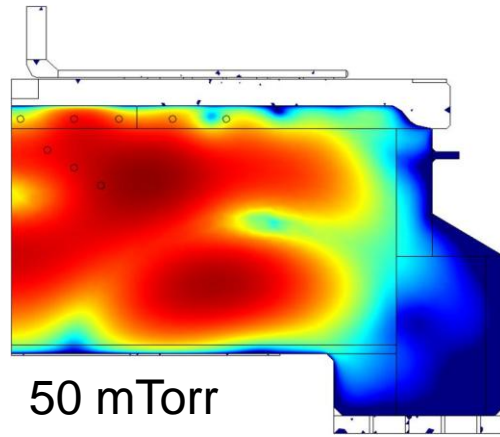
Convergence abruptly by mode change – model settings (mesh, time step) do not allow fast transition on numerical side



Color scale is same for all plots in range from 0 to 4 Wm⁻³

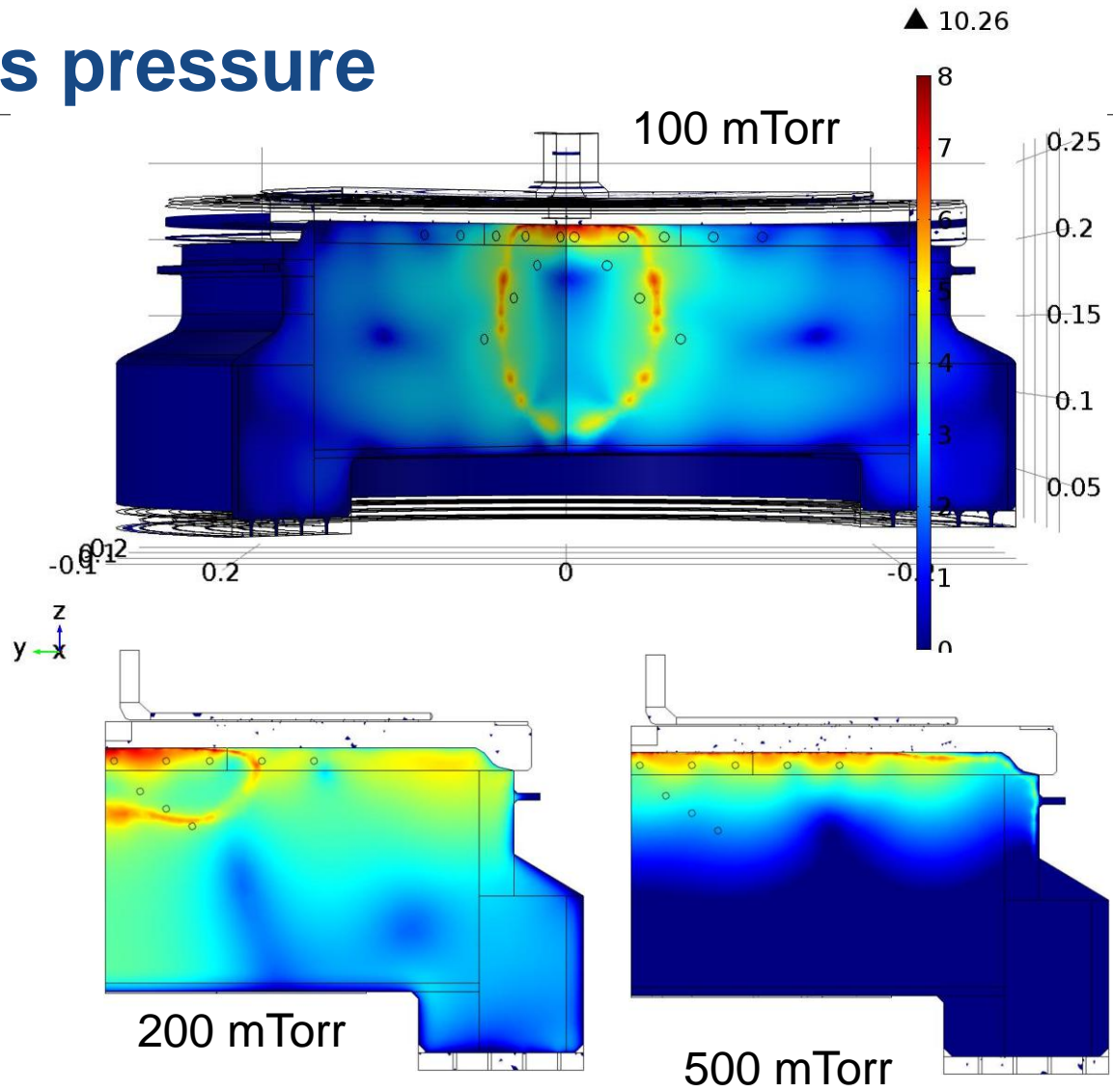
18

Resistive loss vs pressure



5 % H₂ in Ar plasma

Conversion from transitional/resonant mode into SW mode

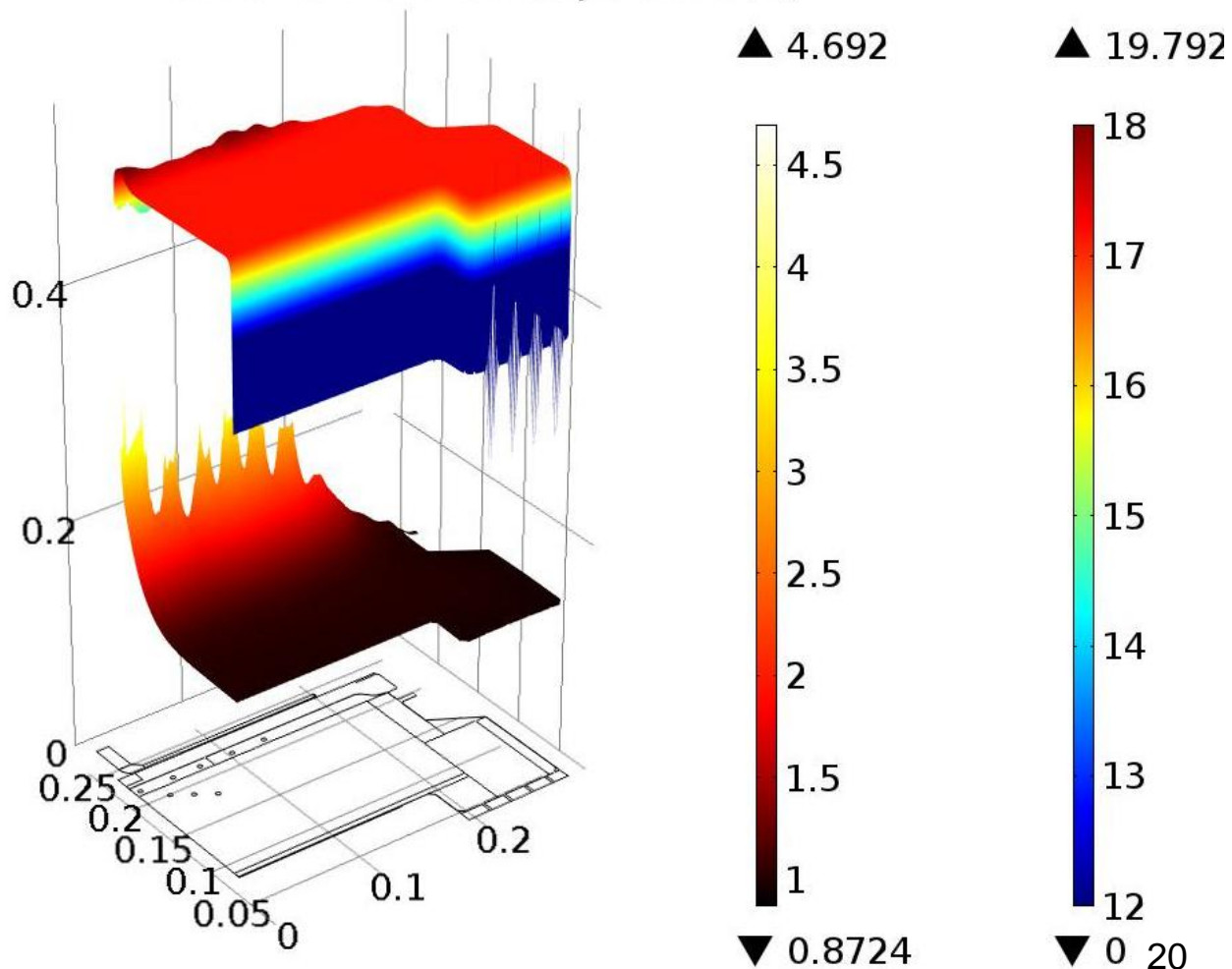


Color scale is same for all plots in range from 0 to 4 Wm⁻³ 19

5% H₂ + Ar mixture

Surface: log₁₀(mwp.ne) Streamline: Velocity field
Surface: Electron temperature (V)

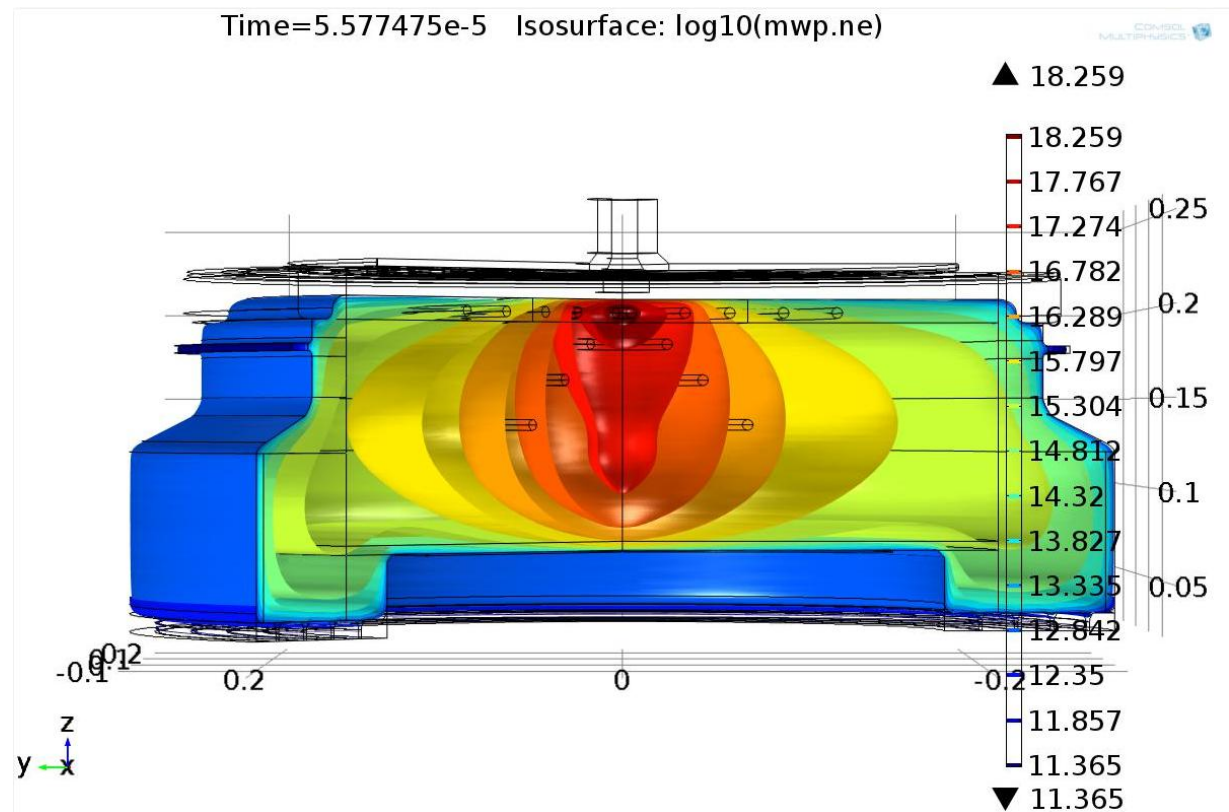
- surface plots of electron density, n_e , and electron temperature, T_e ,
- total flow 400 sccm
- microwave power 3.5 kW
- 500 mTorr
- converged case



Plasma density

Ar+H₂+SiH₄

100 mTorr

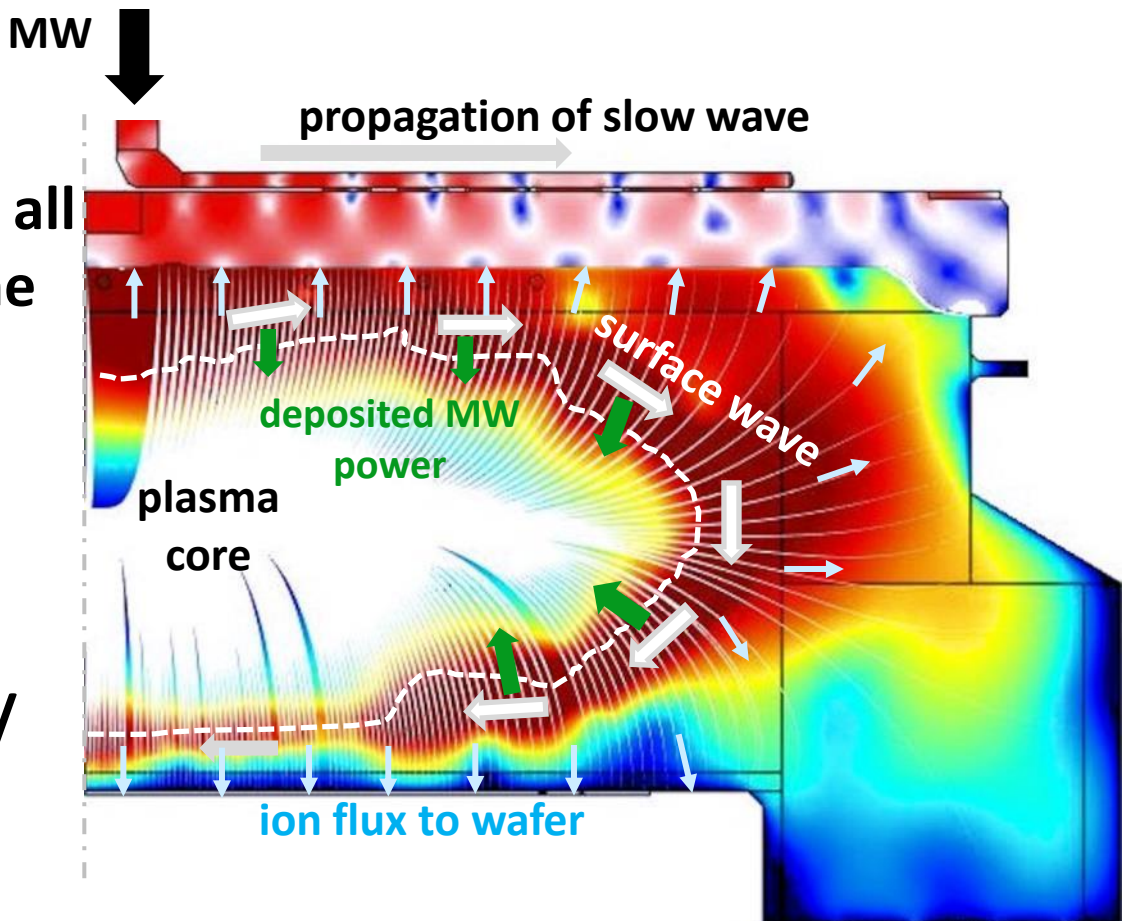


Iso-surface plot of electron density (n_e , m⁻³)

Hydrogen and silane flows were sustained at low level to enable convergence

comprehensive and approachable assessment

- To show and interpret all phenomena within one framework
- Coupled physics and chemistry
- Accessible to process / hardware engineer, marketing, customer



Final remark

- Physics modes transition due to wave-plasma coupling may creates problems that separately are solvable but in fast transient need special prevention to overcome (over-dense meshing, extremely short time steps)

Questions?

Thank you!

Plasma spatial distribution

Operation modes

Surface wave mode

OVER-DENSE PLASMA

Transfer mechanism allows generation of over-dense plasmas with electron densities beyond the critical density (above $\sim 3 \times 10^{17} \text{ m}^{-3}$)

The conductivity of the plasma enables the wave to propagate along the plasma surface

The SW mode allows generation of uniform plasmas over several wavelengths of the EM wave (in vacuum $\lambda \sim 12.2 \text{ cm}$)

Transitional mode

BELOW CUT-OFF DENSITY

$\sim 7.5 \times 10^{16} \text{ m}^{-3}$

EM wave is partially traversing the plasma

Both reactor geometry and dense plasma structure interplay and form final spatio-temporal distribution

Resonant mode

VERY LOW DENSITY

When plasma density does not exceed the critical density a standing EM wave is confined by a reactor (resonator cavity) and penetrates the plasma which is sustained by wave in the regions of highest field intensity

Listing from model tree

volume

- Species: e
 - Species: Ar
 - Species: Ar+
 - Species: Ars
 - Species: Arms
 - Species: H2
 - Species: H
 - Species: H+
 - Species: H2+
 - Species: H3+
 - Species: H2exc
 - Species: Hexc
 - Species: SiH4
 - Species: SiH4+
 - Species: SiH3+
 - Species: SiH2+
 - Species: SiH+
 - Species: Si+
 - Species: SiH4-
 - Species: SiH4exc
 - Species: SiHexc
 - Species: Siexc
 - Species: SiH3
 - Species: SiH2
 - Species: SiH
 - Species: Si
 - Species: Si2H6
 - Species: Si2H5
- 1: $e+Ar \Rightarrow e+Ar$
 - 2: $e+Ar \Rightarrow e+Arms$
 - 3: $e+Arms \Rightarrow e+Ar$
 - 4: $e+Ar \Rightarrow 2e+Ar+$
 - 5: $e+Arms \Rightarrow 2e+Ar+$
 - 46: $e+Arms \Rightarrow e+Ars$
 - 47: $e+Ar+ \Rightarrow Arms$
 - 48: $e+Ar \Rightarrow e+Ars$
- 8: $e+H2 \Rightarrow 2e+0.07H+0.07H++0.93H2+$
 - 43: $e+H2 \Rightarrow 3e+2H+$
 - 9: $e+H2 \Rightarrow e+H2$
 - 10: $e+H2 \Rightarrow e+H2exc$
 - 11: $e+H2 \Rightarrow e+H2exc$
 - 12: $e+H2 \Rightarrow e+H2exc$
 - 13: $e+H2 \Rightarrow e+H2exc$
 - 14: $e+H2 \Rightarrow e+H2exc$
 - 15: $e+H2 \Rightarrow e+H2exc$
 - 16: $e+H2 \Rightarrow e+H2exc$
 - 17: $e+H2 \Rightarrow e+H2exc$
 - 18: $e+H2 \Rightarrow e+H2exc$
 - 19: $e+H2 \Rightarrow e+H2exc$
 - 20: $e+H2 \Rightarrow e+H2exc$
 - 21: $e+H2 \Rightarrow e+H2exc$
 - 22: $e+H2 \Rightarrow e+H2exc$
 - 23: $e+H2 \Rightarrow e+H2exc$
 - 24: $e+H2 \Rightarrow e+2H$
 - 25: $e+H2 \Rightarrow e+2H$
 - 26: $e+H2 \Rightarrow e+2H$
 - 27: $e+H2 \Rightarrow e+2H$
 - 28: $e+H2 \Rightarrow e+2H$
 - 35: $e+H \Rightarrow 2e+H+$
 - 36: $e+H \Rightarrow e+H$
 - 37: $e+H \Rightarrow e+Hexc$
 - 38: $e+H \Rightarrow e+Hexc$
 - 39: $e+H \Rightarrow e+Hexc$
 - 40: $e+H \Rightarrow e+Hexc$
 - 41: $e+H \Rightarrow e+Hexc$
- 50: $e+SiH4 \Rightarrow e+SiH4$
 - 51: $e+SiH4 \Rightarrow e+SiH4exc$
 - 52: $e+SiH4 \Rightarrow e+SiH4exc$
 - 53: $e+SiH4 \Rightarrow e+SiH4exc$
 - 54: $e+SiH4 \Rightarrow e+SiH4exc$
 - 55: $e+SiH4 \Rightarrow 2e+SiH4+$
 - 56: $e+SiH4 \Rightarrow SiH4-$
 - 57: $e+SiH4 \Rightarrow 2e+SiH2++H2$
 - 58: $e+SiH4 \Rightarrow 2e+SiH3++H$
 - 59: $e+SiH4 \Rightarrow 2e+Si++2H2$
 - 60: $e+SiH4 \Rightarrow 2e+SiH++H2+H$
 - 61: $e+SiH4 \Rightarrow 2e+SiH2+H2+$
 - 62: $e+SiH4 \Rightarrow 2e+SiH+H+$
 - 63: $e+SiH4 \Rightarrow e+SiH3+H$
 - 64: $e+SiH4 \Rightarrow e+SiH2+2H$
 - 65: $SiH4exc \Rightarrow SiHexc+H2+H$
 - 69: $e+SiH4 \Rightarrow e+SiH+H2+H$
 - 70: $e+SiH4 \Rightarrow e+Siexc+2H2$
 - 71: $e+SiH4 \Rightarrow e+SiHexc+2H2+H$
 - 91: $e+SiH+ \Rightarrow Si+H$
 - 92: $e+SiH2+ \Rightarrow SiH+H$
 - 93: $e+SiH3+ \Rightarrow Si+H2+H$
 - 94: $e+SiH2 \Rightarrow 2e+SiH2+$
 - 95: $e+SiH3 \Rightarrow 2e+SiH3+$
 - 96: $e+SiH \Rightarrow 2e+SiH+$
 - 97: $e+Si \Rightarrow 2e+Si+$

surface

- Species: Si(s)
 - Species: Si(b)
 - Species: SiH(s)
- 1: $Ars \Rightarrow Ar$
 - 2: $Ar+ \Rightarrow Ar$
 - 28: $Arms \Rightarrow Ar$
 - 4: $H2exc \Rightarrow H2$
 - 26: $Hexc \Rightarrow 0.5H2$
 - 24: $H \Rightarrow 0.5H2$
 - 25: $H+ \Rightarrow 0.5H2$
 - 3: $H2+ \Rightarrow H2$
 - 27: $H3+ \Rightarrow 1.5H2$
 - 29: $SiH4exc \Rightarrow SiH4$
 - 30: $SiH4+ \Rightarrow SiH4$
 - 33: $SiH3+ \Rightarrow SiH3$
 - 32: $SiH2+ \Rightarrow SiH2$
 - 34: $SiH+ \Rightarrow SiH$
 - 31: $SiH- \Rightarrow SiH4$
 - 39: $SiH4+2Si(s) \Rightarrow Si(b)+2SiH(s)+H2$
 - 40: $SiH(s) \Rightarrow Si(s)+0.5H2$